General Purpose Transistor

PNP Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-416/SC-75 which is designed for low power surface mount applications.

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device



Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V _{CEO}	-45	V
Collector-Base Voltage	V _{CBO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current – Continuous	Ic	-100	mAdc
Collector Current – Peak	Ic	-200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) T _A = 25°C Derated above 25°C	P _D	200 1.6	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	600	°C/W
Total Device Dissipation, FR-4 Board (Note 2) T _A = 25°C Derated above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	400	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

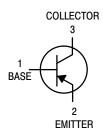
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 @ min pad.
- 2. FR-4 @ 1.0 × 1.0 in pad.



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CASE 463 SOT-416 STYLE 1

MARKING DIAGRAM



3F = Device Code

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•				
Collector-Emitter Breakdown Voltage (I _C = -10 mA)	V _{(BR)CEO}	-45	-	-	V
Collector – Emitter Breakdown Voltage (I _C = –10 μA, V _{EB} = 0)	V _{(BR)CES}	-50	_	-	V
Collector – Base Breakdown Voltage (I _C = –10 μA)	V _{(BR)CBO}	-50	-	-	V
Emitter – Base Breakdown Voltage (I _E = –1.0 μA)	V _{(BR)EBO}	-5.0	_	-	V
Collector Cutoff Current ($V_{CB} = -30 \text{ V}$) ($V_{CB} = -30 \text{ V}$, $T_A = 150^{\circ}\text{C}$)	I _{CBO}	-	_ _	-15 -4.0	nA μA
ON CHARACTERISTICS	·				
DC Current Gain $(I_C = -10 \mu A, V_{CE} = -5.0 \text{ V})$ $(I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$	h _{FE}	- 220	150 290	- 475	-
Collector – Emitter Saturation Voltage ($I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$) ($I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$)	V _{CE(sat)}	- -	_ _	-0.3 -0.65	V
Base – Emitter Saturation Voltage (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{BE(sat)}	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage ($I_C = -2.0$ mA, $V_{CE} = -5.0$ V) ($I_C = -10$ mA, $V_{CE} = -5.0$ V)	V _{BE(on)}	-0.6 -	_ _	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = –10 mA, V _{CE} = –5.0 Vdc, f = 100 MHz)	f _T	100	_	_	MHz
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)	C _{ob}	-	-	4.5	pF
Noise Figure $ \text{(I}_{\text{C}} = -0.2 \text{ mA, V}_{\text{CE}} = -5.0 \text{ Vdc, R}_{\text{S}} = 2.0 \text{ k}\Omega, \\ \text{f} = 1.0 \text{ kHz, BW} = 200 \text{ Hz)} $	NF	-	_	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

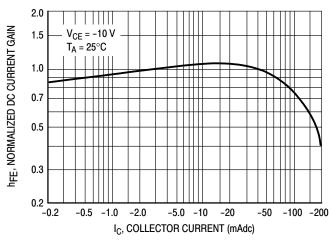


Figure 1. Normalized DC Current Gain

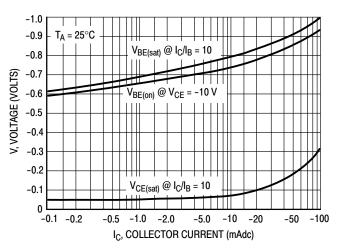


Figure 2. "Saturation" and "On" Voltages

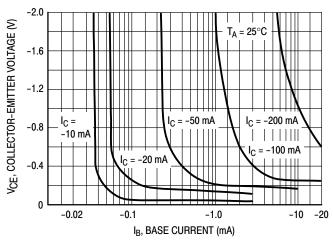


Figure 3. Collector Saturation Region

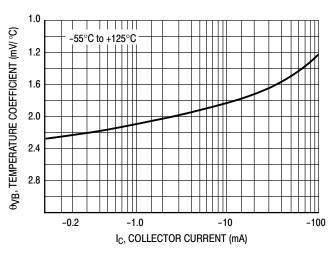


Figure 4. Base-Emitter Temperature Coefficient

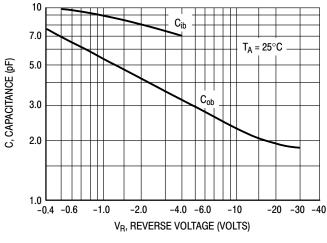


Figure 5. Capacitances

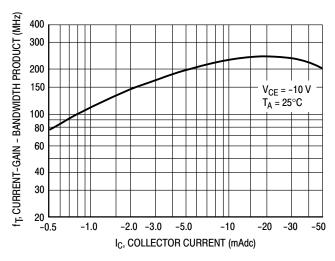


Figure 6. Current-Gain - Bandwidth Product

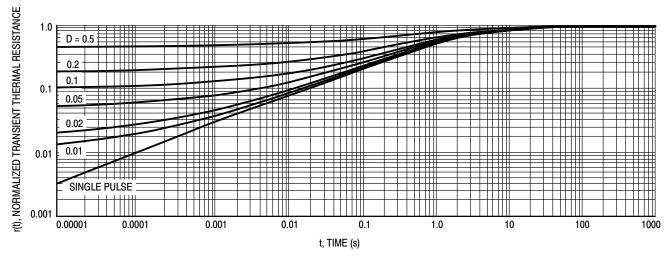


Figure 7. Thermal Response

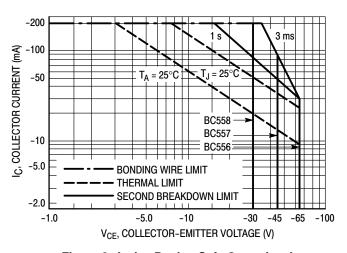


Figure 8. Active Region Safe Operating Area

The safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 8 is based upon $T_{J(pk)} = 150^{\circ}C$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 7. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

ORDERING INFORMATION

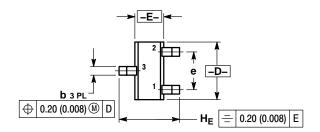
Device	Package	Shipping [†]		
BC857BTT1G	SOT-416	2 000 / Tana 9 Dagi		
NSVBC857BTT1G*	(PB-Free)	3,000 / Tape & Reel		

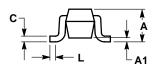
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SOT-416 (SC-75) **CASE 463** ISSUE F



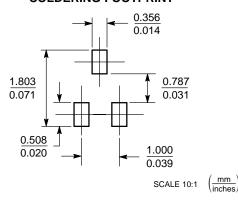


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
- CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.061	0.063	0.065

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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